



# MBR1020FCT THRU MBR1060FCT

## Schottky Diodes

### Features

- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Gu nd JESD22-B102

**Polarity:** As marked

### Maximum Ratings (T<sub>a</sub>=25 Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR1020FCT	MBR1035FCT	MBR1045FCT	MBR1050FCT	MBR1060FCT
Device marking code			MBR1020FCT	MBR1035FCT	MBR1045FCT	MBR1050FCT	MBR1060FCT
Repetitive Peak Reverse Voltage	VRRM	V	20	35	45	50	60
Average Rectified Output Current @60Hz sine wave, R-load, T <sub>a</sub> =25	I <sub>O</sub>	A	10				
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, T <sub>a</sub> =25	IFSM	A	100				
Current Squared Time @1ms t<8.3ms T <sub>j</sub> =25	I <sup>2</sup> t	A <sup>2</sup> s	41				
Storage Temperature	T <sub>stg</sub>		-55 ~ +150				
Junction Temperature	T <sub>j</sub>		-55 ~ +125			-55 ~ +150	

### Electrical Characteristics T<sub>a</sub>=25 Unless otherwise specified

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR1020FCT	MBR1035FCT	MBR1045FCT	MBR1050FCT	MBR1060FCT
Maximum instantaneous forward voltage drop per diode	VFM	V	IFM=5.0A	0.55			0.75	
Maximum DC Current	IRRM1	mA	VRM=VRRM T <sub>a</sub> =25	0.2				
			VRM=VRRM T <sub>a</sub> =100	20				



## MBR1020FCT THRU MBR1060FCT

**Thermal Characteristics**  $T_a=25$  Unless otherwise specified

PARAMETER		SYMBOL	UNIT	MBR1020FCT	MBR1035FCT	MBR1040FCT	MBR1050FCT	MBR1060FCT
Thermal Resistance	Between junction and case	R J-C	$^{\circ}W$	4.0				

**Ordering Information (Example)**

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QU
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## Outline Dimensions